

□ 2 3 4 5 6 7 8 9 10 11 12

⊙ Pending


Active

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L1: {50} (((((dop$4 impur$3 (ion near3 implant$3) diffus$4) ) near6 (fir

```

Failed

 Saved

- ✎ S1: (1) 09/948877
- ✎ S2: (1736) \*KONINKLIJKE PHILIPS\*.as.
- ✎ S3: (0) 10/753914
- ✎ S4: (1) 10/728910
- ✎ S5: (290) (finfet fin adj2 (fet mosfet mos transistor) )
- ✎ S6: (1) 10/428897
- ✎ S7: (4) (\*6318305\* \*4996574\*).pn.
- ✎ S8: (2) (\*6318305\* \*4996574 6445017\*).pn.
- ✎ S9: (6) (\*6318305\* \*4996574\* \*6445017\*).pn.
- ✎ S10: (1) 10/614052
- ✎ S11: (0) \*6812119\*.pn.
- ✎ S12: (82503) (SRAM static adj3 memory static adj RAM)

CLASSIFICATION: UNCLASSIFIED

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[broad sword] 139

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(((((dop$4 impunit$3 (ion near3 implant$3) diffus$4)
) near6 (fin body)) and ((finfet fin adj2 (fet mosfet mos transistor) )
)) and (fin near8 body)) and ((@ad @pd) <"20031208")
```

Feb. 2005

	U	Inventor	Document ID	Issue P	Title	Curran	Current X	Retrieval S	C	P	Image Doc P
1		Yeo, Yee-CUS	20040099885	2004	1 CMOS SRAM cell configured using mu	257/20					US 20040
2		Fried, Davi	US 20030102518	2003	2 Finfet SRAM cell using low mobility pla	257/40 257/350;					US 20030
3		Nowak; Ed	US 6794718 B2	2004	1 High mobility crystalline planes in dou	257/34 438/149;					US 67947
4		Fried; Davi	US 6664582 B2	2003	1 Fin memory cell and method of fabrica	257/30 257/310;					US 66645
5		Nowak; Ed	US 6610578 B2	2003	3 Method for forming asymmetric dual g	438/30 257/E21.4					US 66105
6		Yeo, Yee-CUS	20050035415	2005	1 Multiple-gate transistors formed on bul	257/40 438/283					US 20050
7		Yeo, Yee-CUS	20040266077	2004	1 Structure and method for forming the	438/15					US 20040
8		Lee, Jong	US 20040256647	2004	3 Strained silicon finFET device	257/28					US 20040
9		Boyantov, B	US 20040253774	2004	1 Double-gate transistor with enhanced	438/17 438/268					US 20040
10		Pham, Dani	US 20040219722	2004	1 METHOD FOR FORMING A DOUBLE-	438/15 257/401;					US 20040